

Automotive N-Channel 100 V (D-S) 175 °C MOSFET

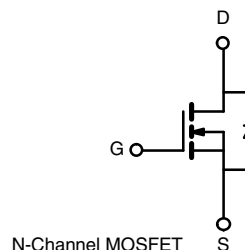
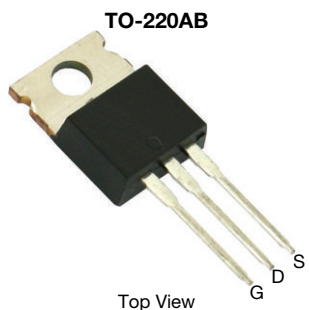
PRODUCT SUMMARY	
V_{DS} (V)	100
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	0.0095
I_D (A)	120
Configuration	Single
Package	TO-220

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified ^d
- 100 % R_g and UIS tested
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE



ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	$T_C = 25$ °C ^a	I_D	120	A
	$T_C = 125$ °C		73	
Continuous Source Current (Diode Conduction) ^a		I_S	120	
Pulsed Drain Current ^b		I_{DM}	480	
Single Pulse Avalanche Current		I_{AS}	73	
Single Pulse Avalanche Energy		E_{AS}	266	mJ
Maximum Power Dissipation ^b	$T_C = 25$ °C	P_D	375	W
	$T_C = 125$ °C		125	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	40	°C/W
Junction-to-Case (Drain)		R_{thJC}	0.4	

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).
- Parametric verification ongoing.



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA		100	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.5	3.0	3.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 100 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 100 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 100 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	120	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A	-	0.0079	0.0095	Ω
		V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0190	
		V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0250	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 30 A		-	99	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	6915	8645	pF
Output Capacitance	C _{oss}			-	635	795	
Reverse Transfer Capacitance	C _{rss}			-	280	350	
Total Gate Charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 50 V, I _D = 85 A	-	120	180	nC
Gate-Source Charge ^c	Q _{gs}			-	30	-	
Gate-Drain Charge ^c	Q _{gd}			-	28.5	-	
Gate Resistance	R _g	f = 1 MHz		0.25	0.7	2.3	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 50 V, R _L = 0.6 Ω I _D ≅ 85 A, V _{GEN} = 10 V, R _g = 2.5 Ω		-	21	32	ns
Rise Time ^c	t _r			-	24	36	
Turn-Off Delay Time ^c	t _{d(off)}			-	52	78	
Fall Time ^c	t _f			-	16	24	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	480	A
Forward Voltage	V _{SD}	I _F = 85 A, V _{GS} = 0		-	0.9	1.5	V

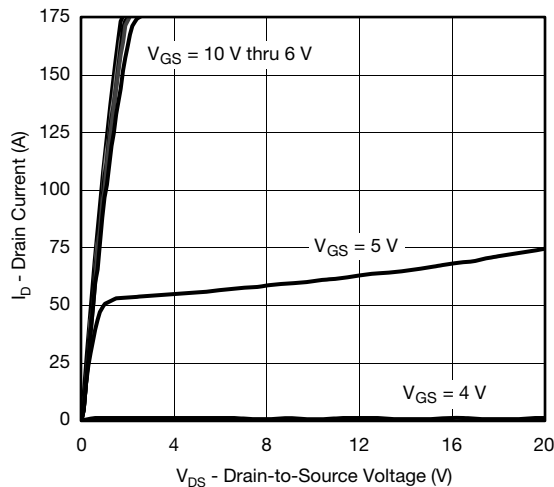
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

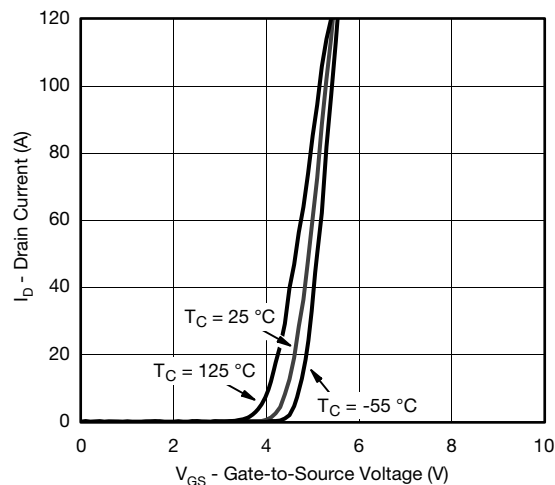
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



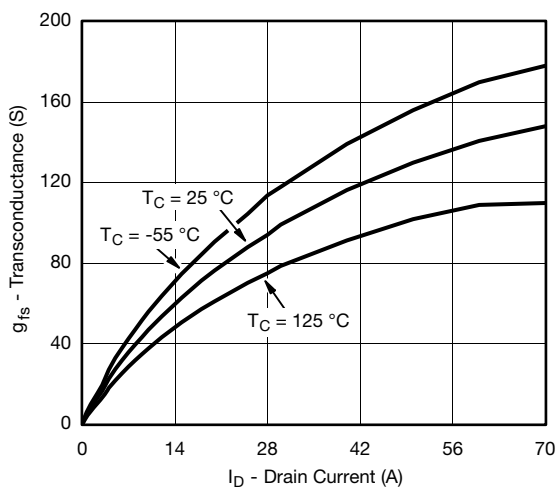
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



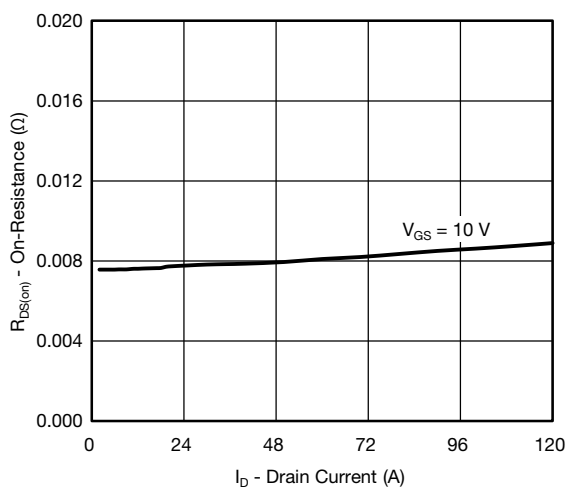
Output Characteristics



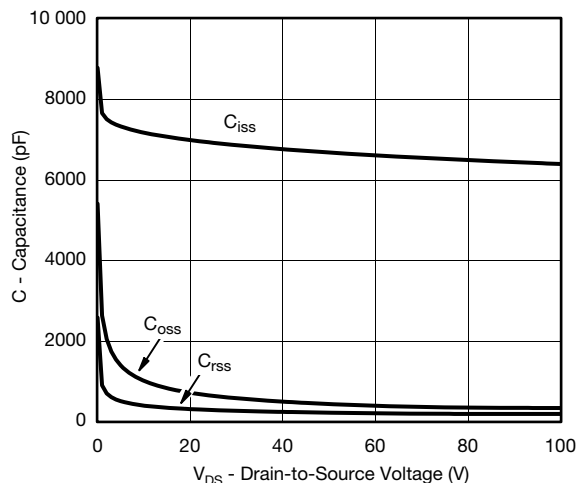
Transfer Characteristics



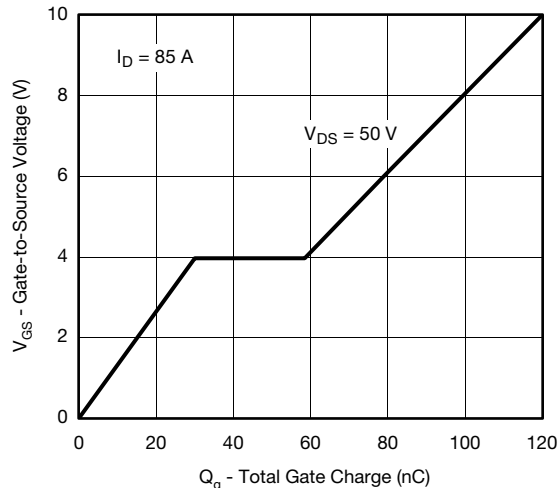
Transconductance



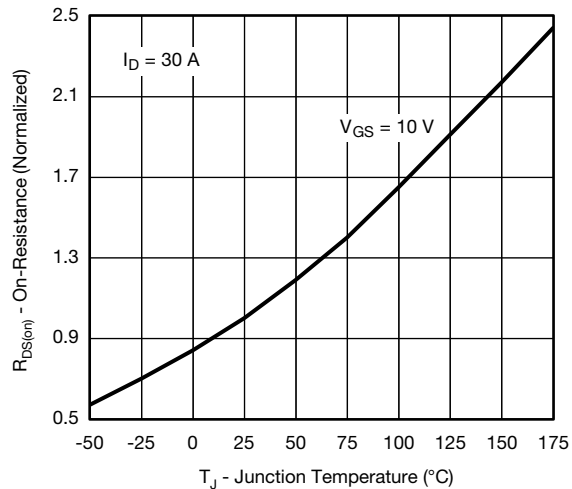
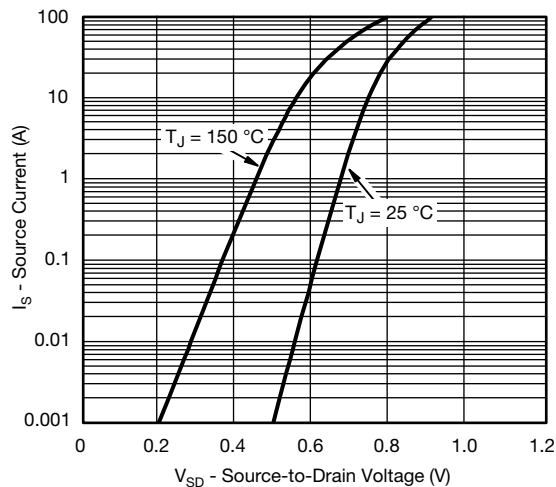
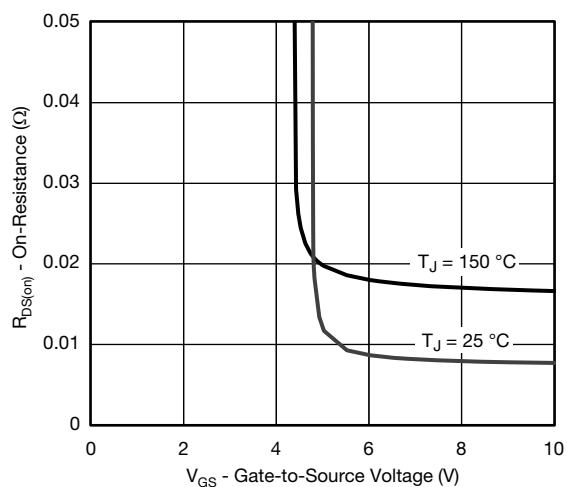
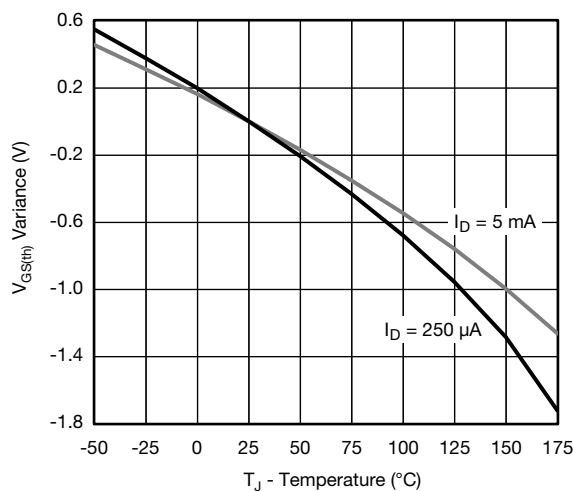
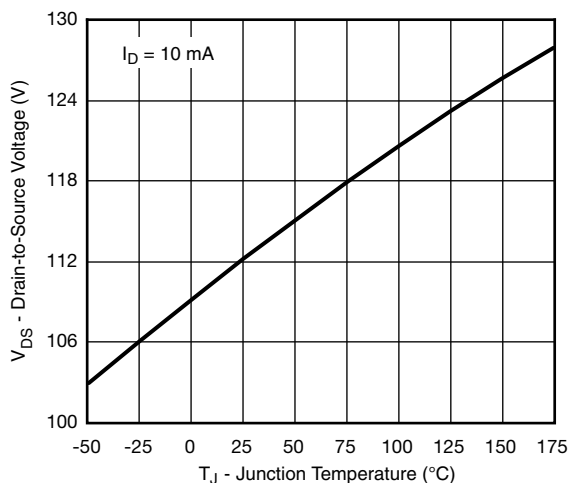
On-Resistance vs. Drain Current



Capacitance

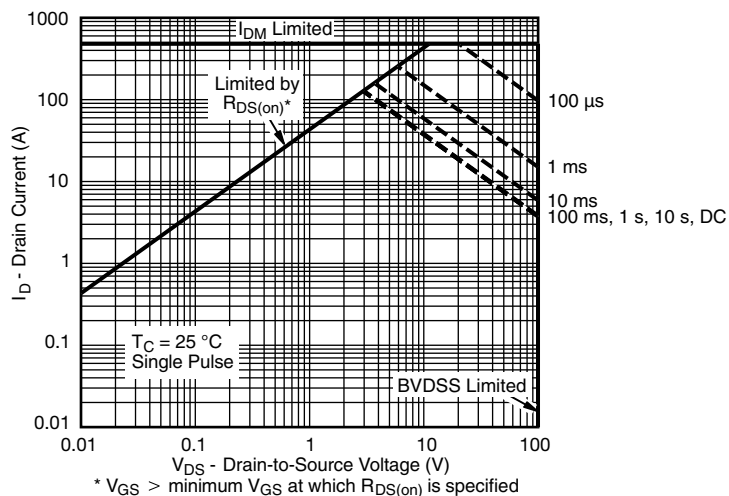


Gate Charge

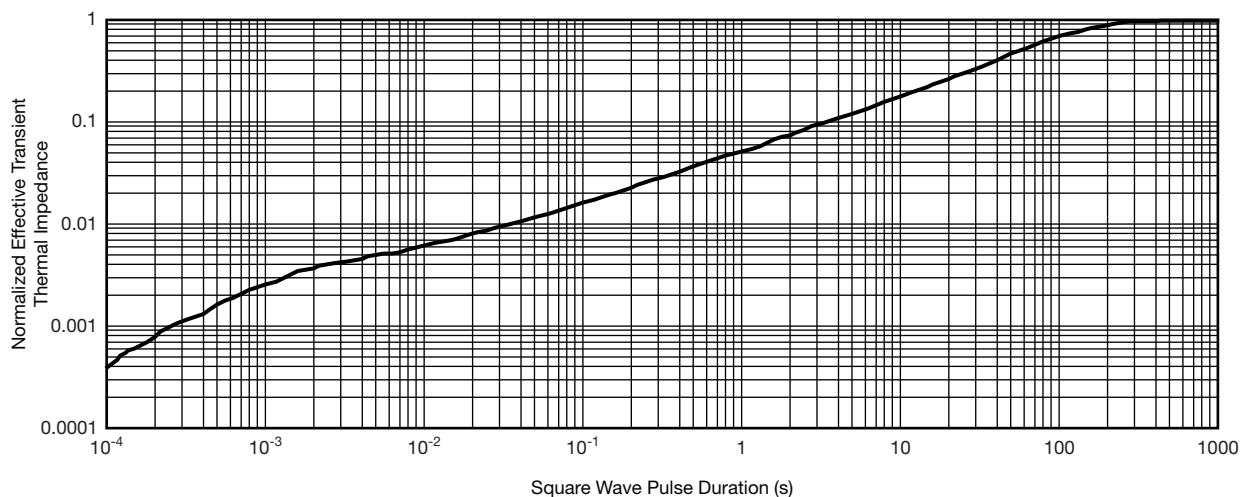
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

On-Resistance vs. Junction Temperature

Source Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



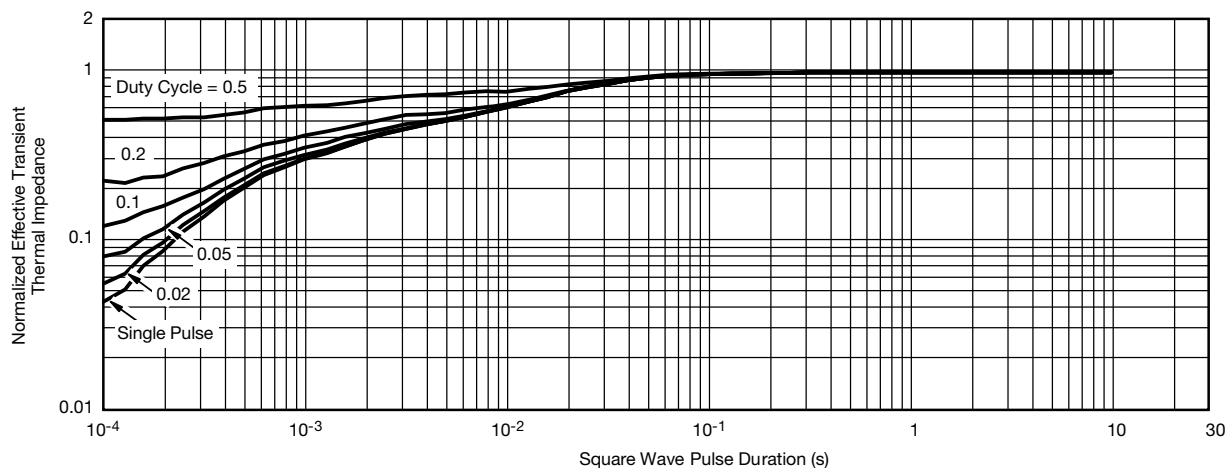
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction to Case ($25\text{ }^{\circ}\text{C}$)are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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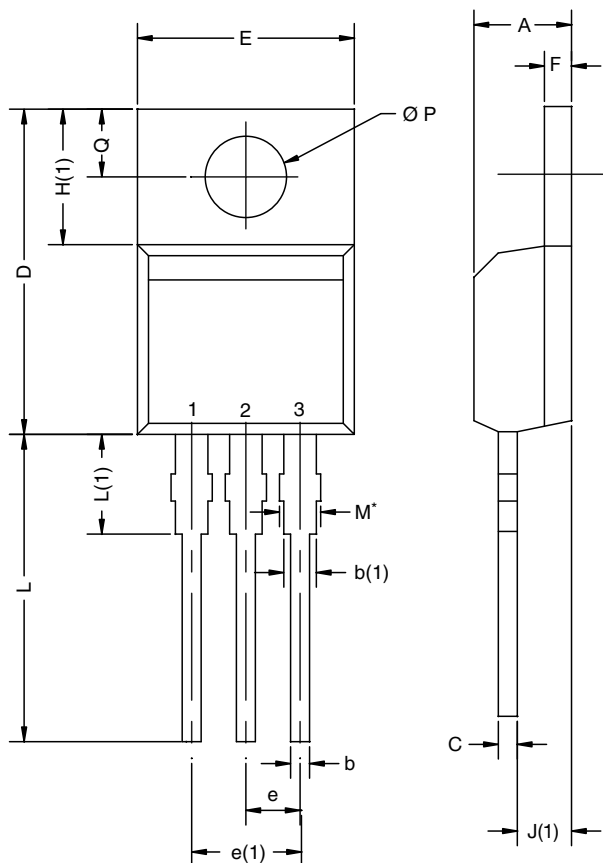
REVISION HISTORY ^a		
REVISION	DATE	DESCRIPTION OF CHANGE
B	04-Aug-15	• Revised R _g minimum limit

Note

a. As of April 2014



TO-220AB

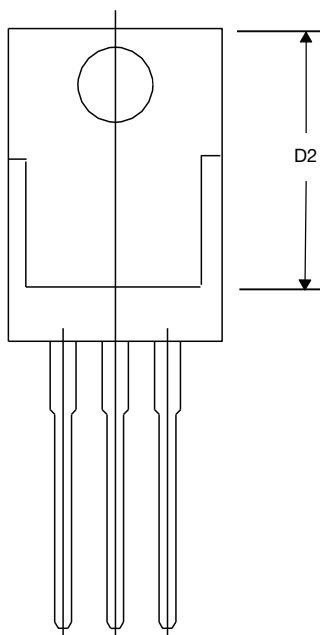


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: T14-0413-Rev. P, 16-Jun-14
DWG: 5471

Note

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM





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